
Irradiation Tests of ROHM 0.35 μ m ASIC and Actel Anti-fuse FPGA for the ATLAS Muon Endcap Level-1 Trigger System

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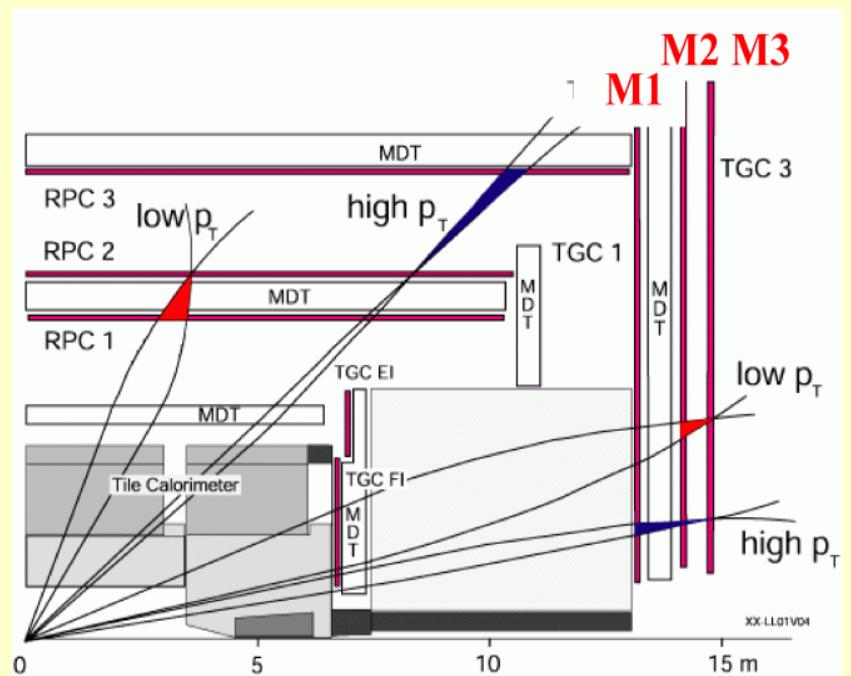
- ◆ TID (γ -ray) and SEE (proton) tests and results for
 - ◆ ROHM and HITACHI 0.35um CMOS
 - ◆ Actel Anti-fuse FPGA series (SX-A, Axcelerator)
 - ◆ LVDS and G-link ser./deser. (Poster)

Introduction

- Most of the ATLAS Endcap Muon Level-1 system will be installed in the detector (On-detector part).
- **Various trigger and readout circuits have been realized with (Three) ASIC chips.**
- **Subsidiary circuits are implemented in FPGA chips.**
- The devices must be hard or tolerant for irradiation of 10 years. This must be confirmed with tests of
 - the ionizing damage (Total Ionizing Dose; TID) with γ -ray
 - the Single Event Effects (SEE) with proton beam (> 60MeV)

ATLAS Muon Endcap Level-1 System

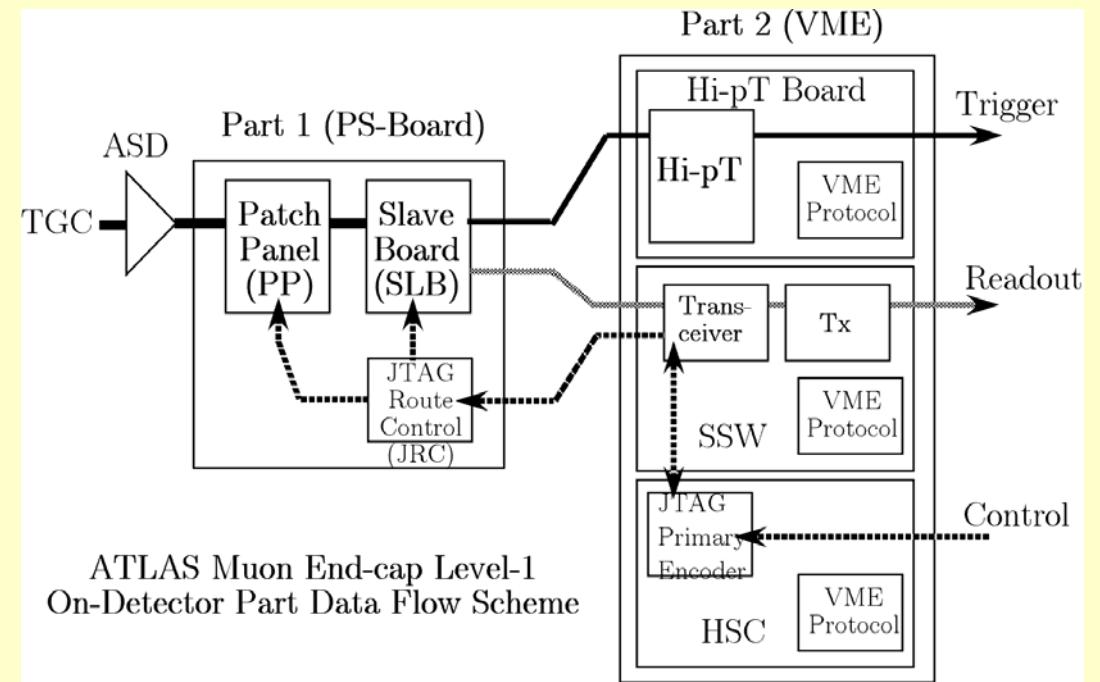
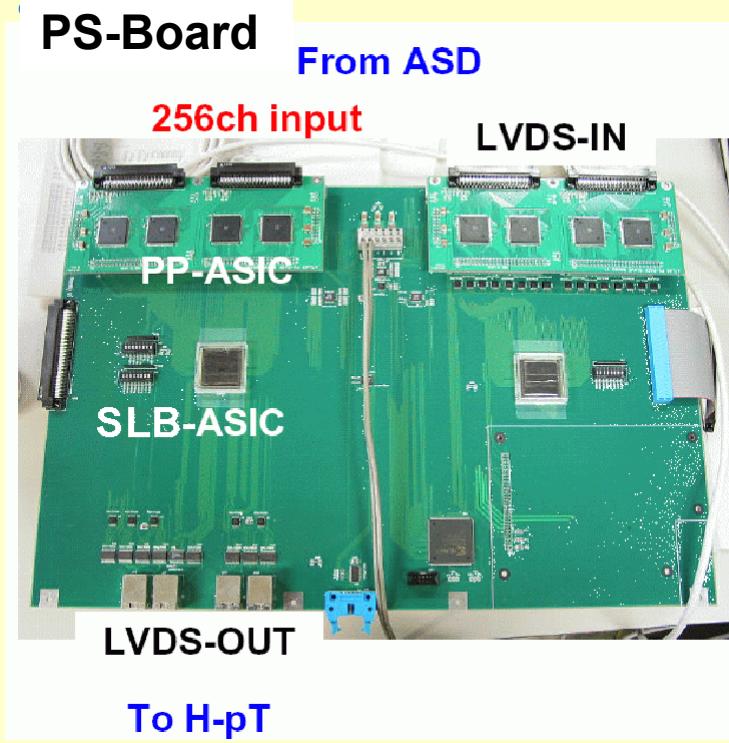
- Thin Gap chambers (TGC) are used to detect muons in the endcap regions ($1.05 \leq \eta \leq 2.70$)
- Hit (on/off) signals of Total 300k channels are processed in the vicinity of the chambers



Level-1 Trigger/Readout System

and FPGA for system

- Two on-detector parts and off-detector part
- On-detector parts
 - PS-board
 - Hi-pt and Star Switch (SSW) (VME) Crate



Devices under Test



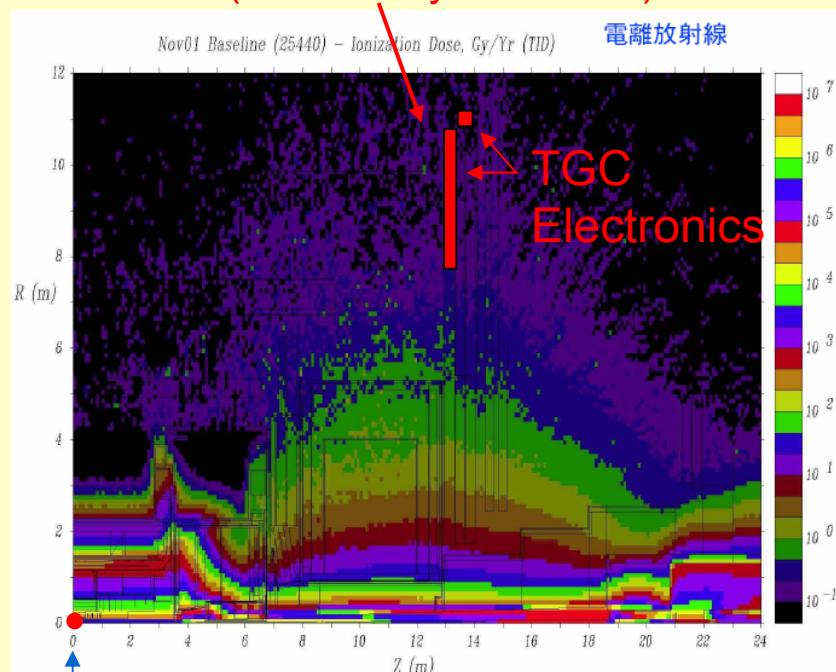
Custom ICs (8 types with 4 technologies)

- ✿ **PP (Patch Panel) ASIC** 0.35um CMOS ROHM
 - ✿ Variable Delay with PLL, LVDS to CMOS, BCID, Test pulse Gen.
- ✿ **SLB (SLave Board) ASIC** 0.35um CMOS ROHM
 - ✿ Low-pT coincidence matrices, Level-1 buffer+ Derandomizer
- ✿ **High-pT (Hi-pT) ASIC** 0.35um HITACHI GA
 - ✿ Hi-pT coincidence matrices
- ✿ **Simple FPGA** Actel Anti-fuse SX-A
 - ✿ JRC (PS board), HSC, VME protocol
- ✿ **FPGA with embeddded memory** Actel Anti-fuse Axcelerator
 - ✿ SSW Transmitter/Receiver
- ✿ *Serial Link IC (LVDS and G-link serdeser)*

Radiation Environment

Ionizing Dose: Gy/year

2-3Gy/10year → 140-210Gy/10year
(with Safety Factor:70)

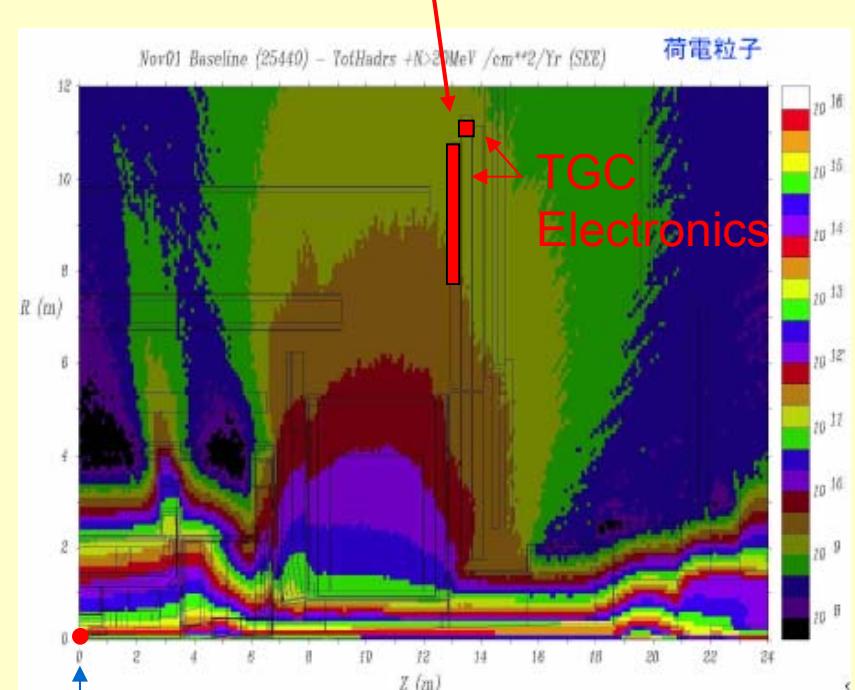


Interaction Point

14/Sept./2004

Total Hadron (>20MeV) :/cm²/year

$1.4-2.8 \times 10^{10}$ hadrons/cm²/10year

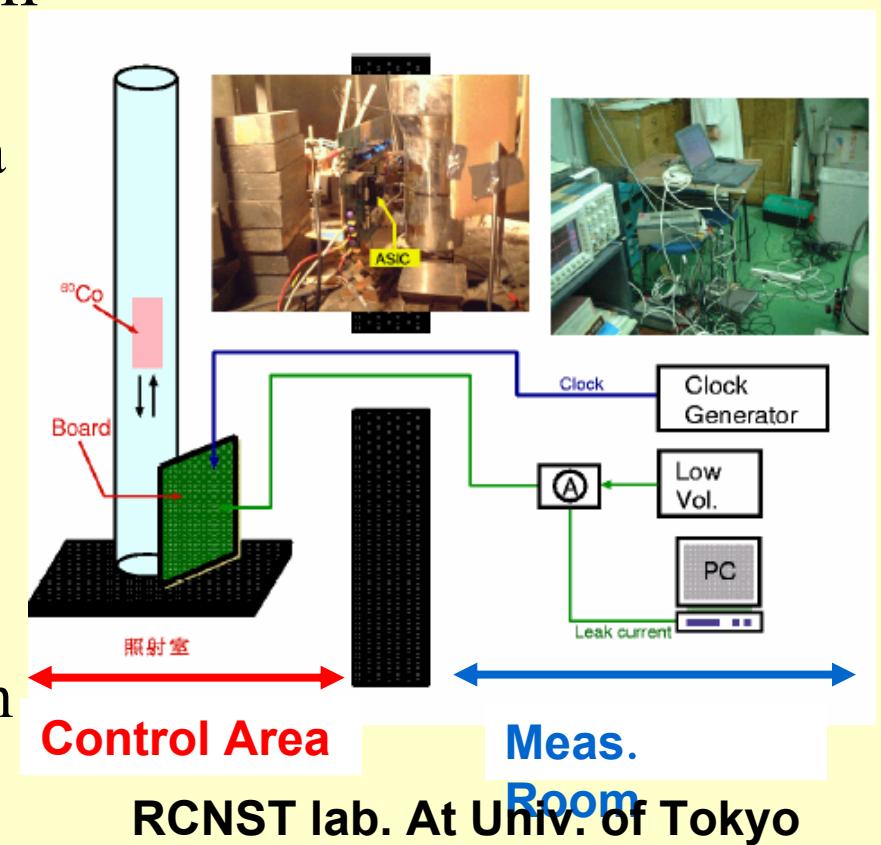


Interaction Point

TID test (γ -ray irradiation)

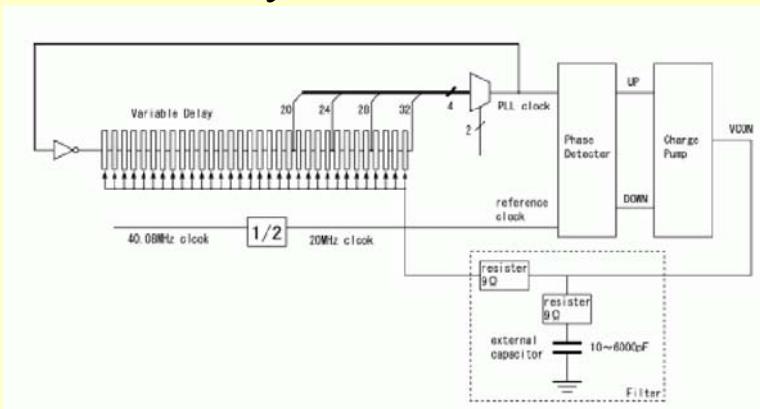
Evaluation of Total Ionization Dose using γ -ray from ^{60}Co

- A DUT (chip) is mounted on a PC board.
- The board is applied with voltage and input signals
- Irradiated 300Gy and more
- Typically 4 samples/DUT
- I_{cc} or Frequency versus Absorbed dose (time) has been evaluated

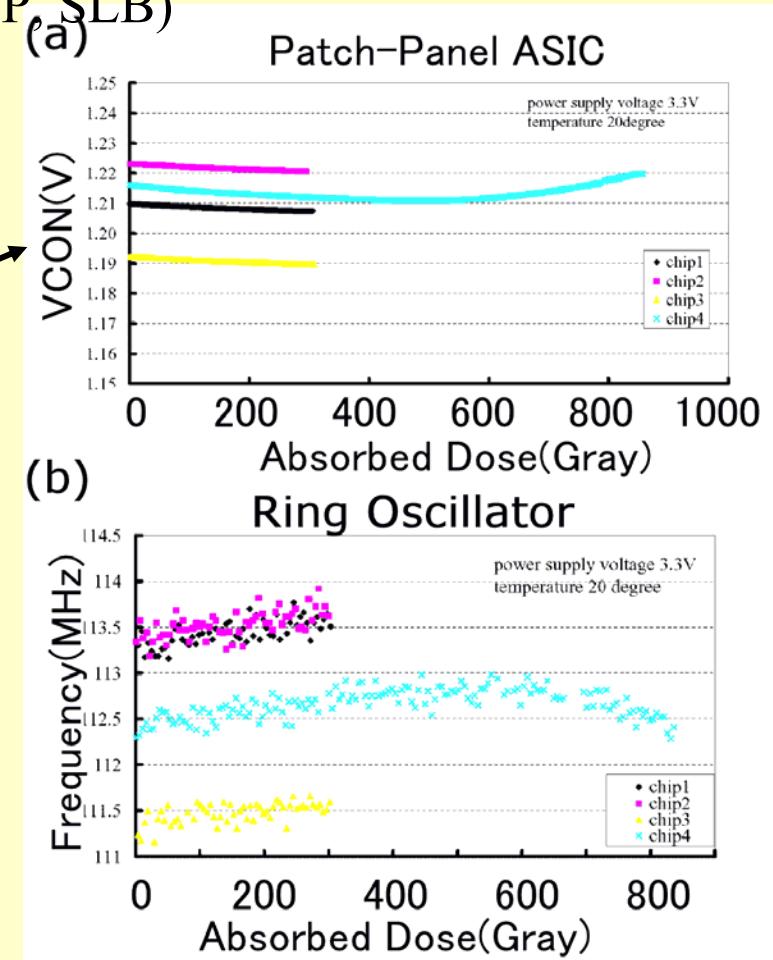
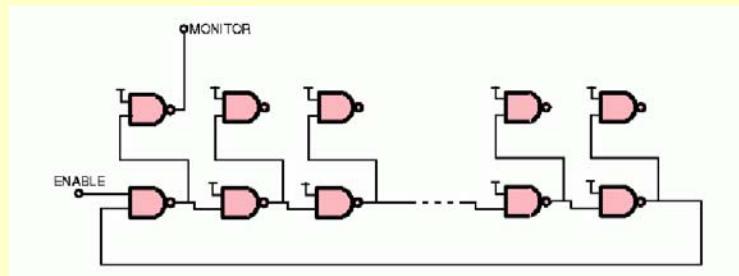


TID test results CMOS ROHM 0.35μm

- 0.35μm ROHM CMOS full custom chip (PP_{SLB})
- PP ASIC VCON(V) of PLL circuit for variable delay

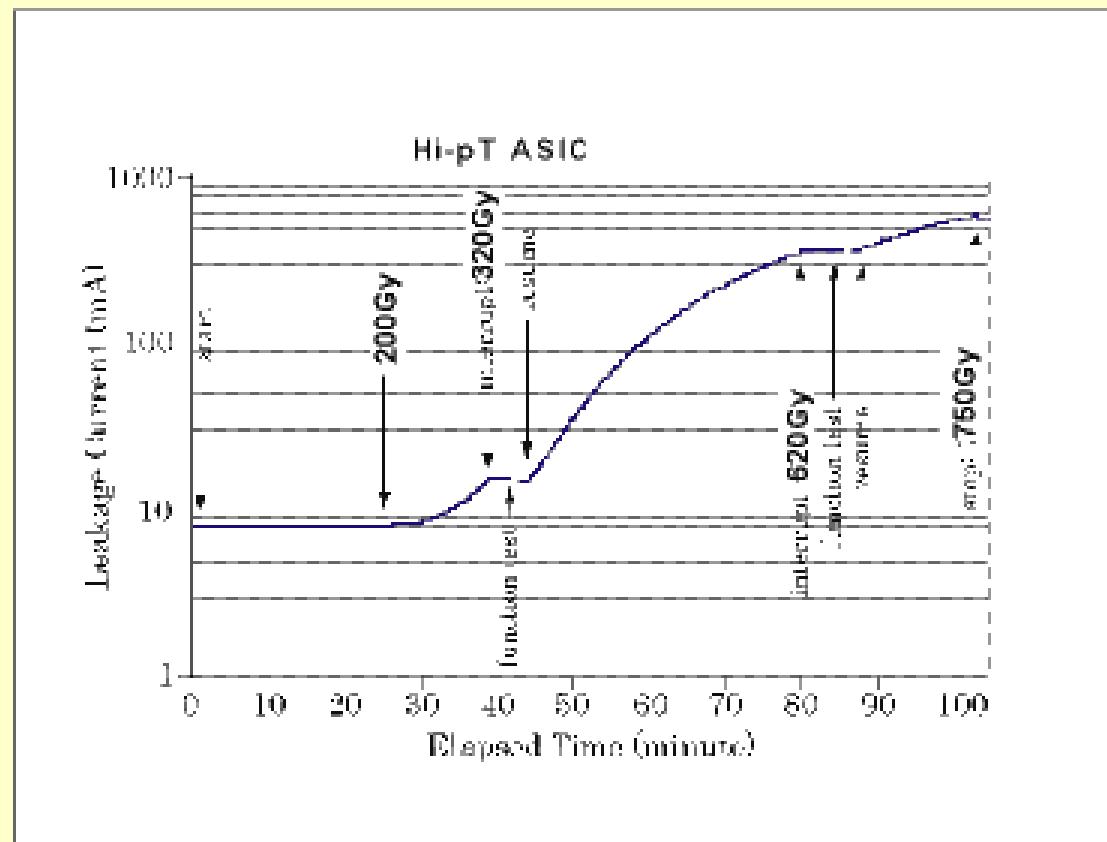


- Special Made Ring Oscillator



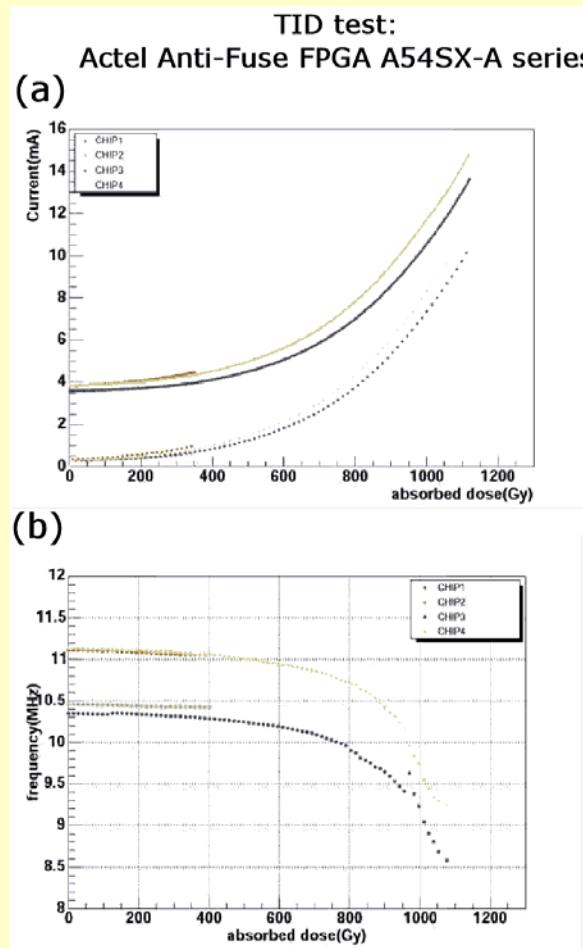
TID test result CMOS Hitachi 0.35 μ m Gate Array (Hi-pT ASIC)

Hi-pT ASIC TID test

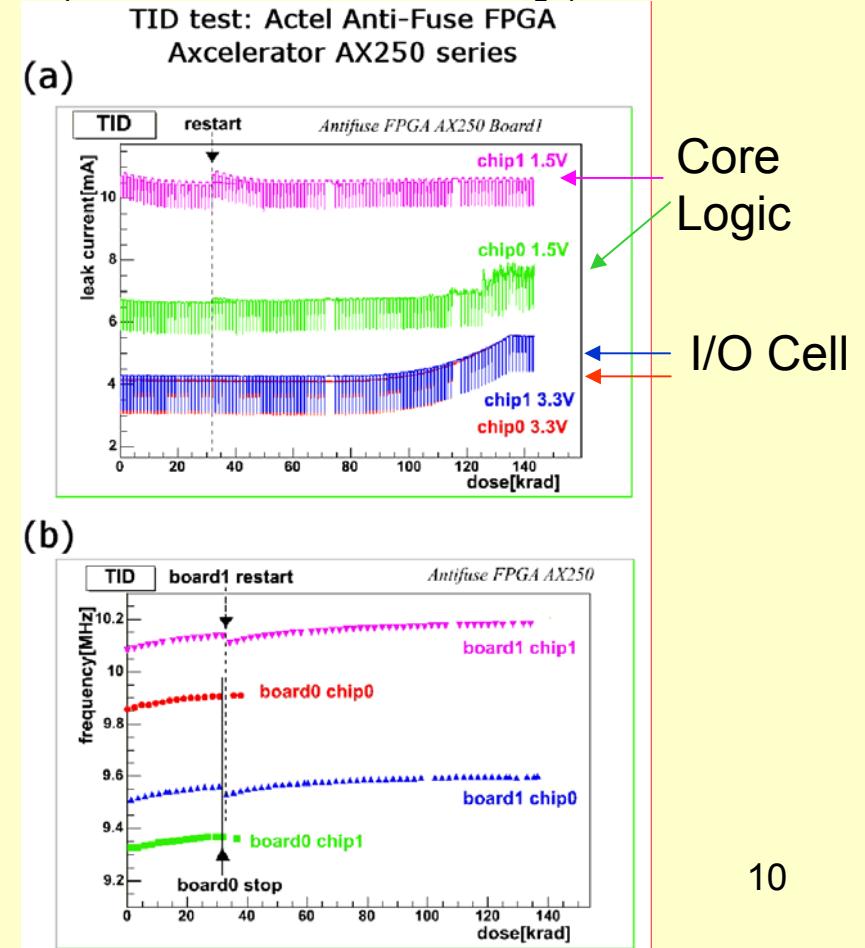


Actel Anti-fuse FPGA series (Ring Oscillator Circuit)

SX-A series



Axcelerator series (embedded memory)



Single Event Effect Test: Proton 70MeV

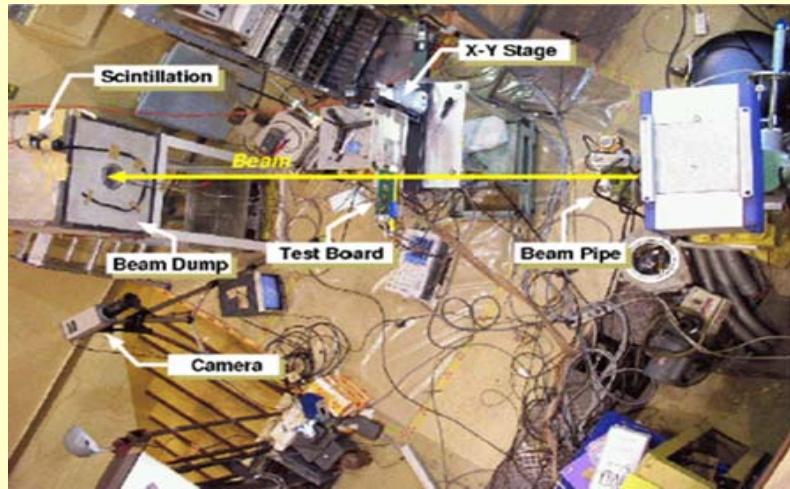
- SEE : Radiation induced bit flip (soft&hard)
- If we know σ_{SEE} for a chip experimentally, we can predict SEE rate with

$$\text{SEE rate} = \sigma_{\text{SEE}} \times \text{Nbits} \times \text{SRLsee} \times \text{SFsim}$$

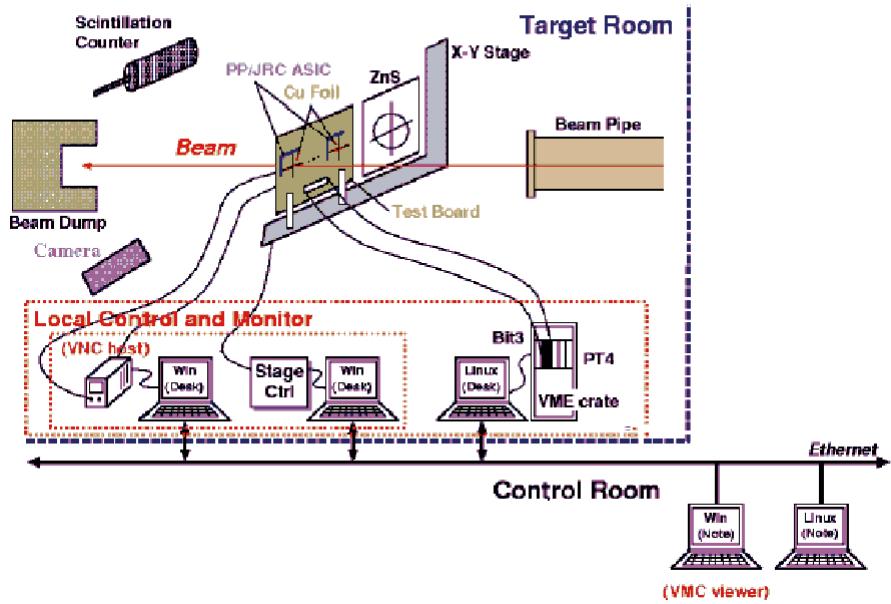
Nbits	Number of Bits	100(Hi-pT)~3000(SLB)
SRLsee	SEE radiation level (hadrons/cm ² /s)	PS board: 2.11x10² HSC VME crate: 1.42x10²
SFsim	Safety Factor	5

SEE test experiment at Tohoku Univ.

- 70 MeV proton beam at Tohoku University Cyclotron (CYRIC) laboratory
- Proton Intensity & beam profile were determined with dosimetry measurement of Cu foils (0.1mm) attached in front of DUT



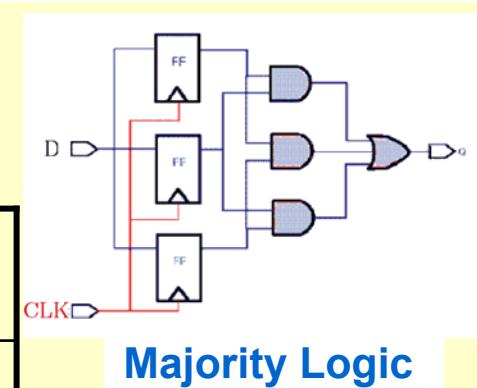
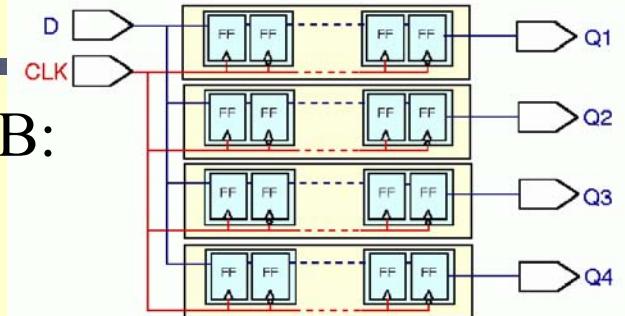
SEE Test Experiment setup for 70MeV Proton Beam



SEE Test results: ASIC

- ★ σ_{SEE} for ROHM 0.35 μm chips for PP, SLB:
 - A special IC was made (4bit shift registers)
- ★ σ_{SEE} for HITACHI 0.35 μm GA
 - JTAG Boundary Scan reg.
- ★ Results: Soft SEE (No hard SEE observed)

Technology	Chip	σ_{SEE} $\text{cm}^{-2}/\text{bit}$	Nbits/Numb. Of chips	SEU rate/day (system)
ROHM 0.35um	PP	2.8×10^{-14}	95/10000	2
ROHM 0.35um	SLB		3007/3000	23
HITACHI 0.35um	Hi-pT	$< 4.7 \times 10^{-15}$	30/1000	< 0.001



w/o majority Logic: It is installed in all the bits in chips

SEE test results: Actel Anti-fuse FPGA

- A54SX-A series: 256 stage 4-bit Shift register
 - No SEE error has been observed with proton fluence of $2.6 \times 10^{12} \text{ proton/cm}^2$
 - $\sigma_{\text{SEE}} < 1.5 \times 10^{-15} (1/\text{cm}^2/\text{bit})$
- Axcelerator AX250 series
 - 345 stage 4-bit Shift registers in R-CELL (FF-cell)
 - 32 SEE with proton fluence of $1.4 \times 10^{12} \text{ proton/cm}^2$
 - $\sigma_{\text{SEE}} = 1.6 \times 10^{-14} (1/\text{cm}^2/\text{bit})$
 - 54Kbit embedded memory (dual port type)
 - 3869 SEE
 - $\sigma_{\text{SEE}} = 4.9 \times 10^{-14} (1/\text{cm}^2/\text{bit})$

Soft SEE only,
No Hard SEE

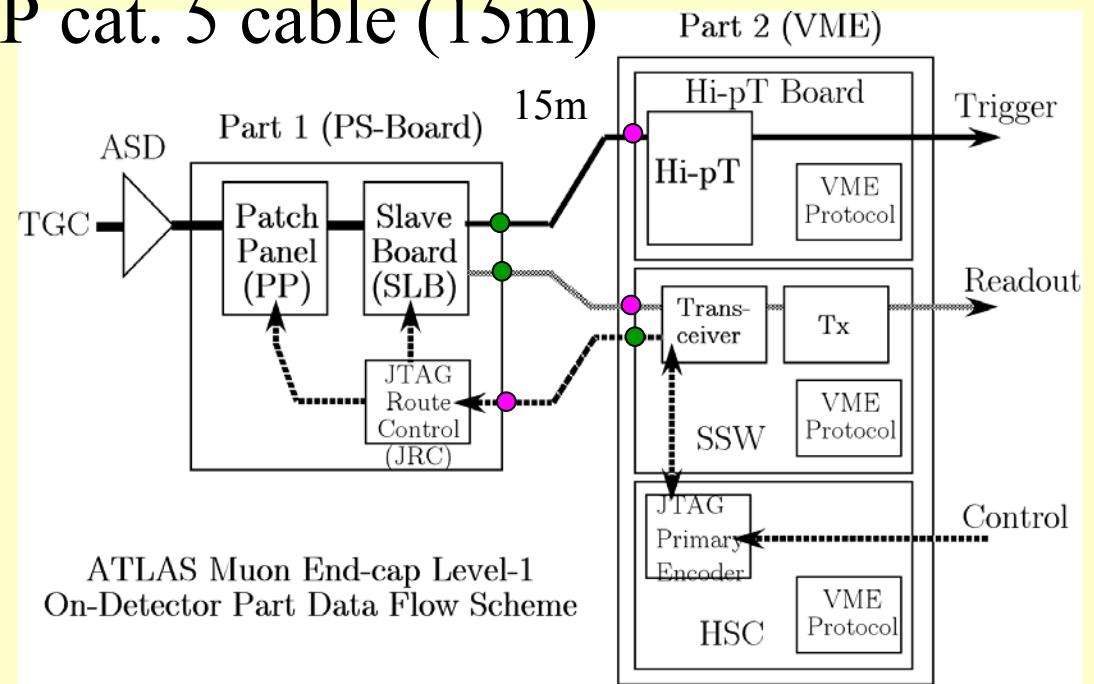
SEE rate for Actel FPGAs in whole system/day <2

LVDS serializer/deserializer

- ★ LVDS serializer and deserializer candidates

- ★ NS:DS65LV1023/1024
- ★ TI:SN65LV1023/1224

- ★ Connected with UTP cat. 5 cable (15m)



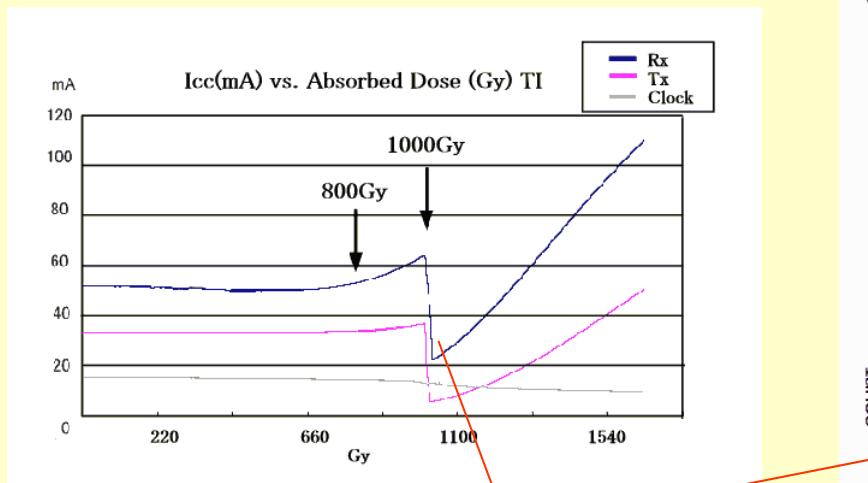
TID and SEE tests of LVDS ser/deser

★ TID test up to 1600Gy

● NS: I_{cc} vs. Dose:

No significant I_{cc} increase

● TI: I_{cc} vs. Dose:



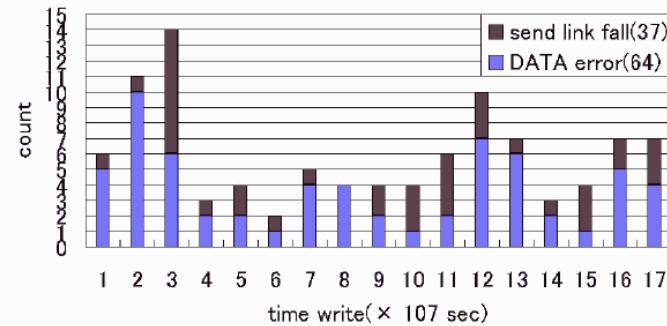
TI chip will be fine
if dose < 1000Gy

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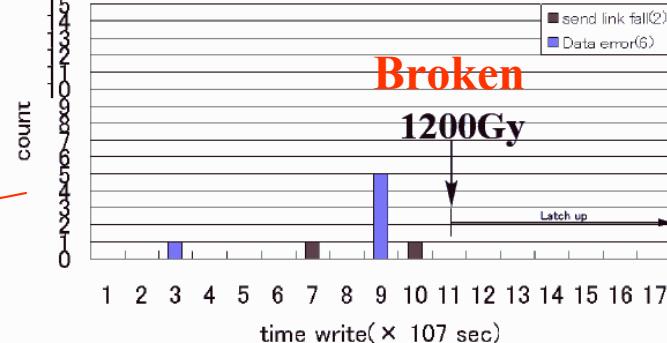
★ SEE test

Time dependence of Error Incidence
during Proton Irradiation

NS Deserializer (Rx)



TI Deserializer (Rx)



Broken

1200Gy

Latch up

Summary

- ✿ ATLAS TGC electronics
 - ✿ TID 140-200Gy/10 years & SEE $\sim 2 \times 10^{10} \text{cm}^2/10\text{years}$
- ✿ γ -irradiation (TID) Test
 - ✿ ASIC/Actel anti-fuse FPGA chips have no problem up to $\sim 1000\text{Gy}$
- ✿ Proton 70MeV irradiation (SEE) Test
 - ✿ Measurement of σ_{SEE} for Soft SEE: rate will be expected as very low
 - ✿ No destructive (hard) SEE like Latch-up has been observed.
- ✿ Link (LVDS, G-link) components
See in detail our Poster presented in this workshop